

August 2010

2N6517 NPN Epitaxial Silicon Transistor

Features

- · High Voltage Transistor
- Collector Dissipation: P_C(max) = 625mW
- Complement to 2N6520
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



Absolute Maximum Ratings $T_a = 25$ °C unless otherwise noted

Symbol	Parameter		Value	Units
V _{CBO}	Collector-Base Voltage	2N6517 2N6517C	350 400	V V
V _{CEO}	Collector-Emitter Voltage	2N6517 2N6517C	350 400	V V
V _{EBO}	Emitter-Base Voltage		6	V
I _C	Collector Current		500	mA
P _C	Collector Power Dissipation		625	mW
T _J	Junction Temperature		150	°C
T _{STG}	Storage Temperature		-55 ~ 150	°C

Electrical Characteristics $T_a = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Max.	Units
BV _{CBO}		$I_{C} = 100 \mu A, I_{E} = 0$ $I_{C} = 100 \mu A, I_{E} = 0$	350 400		V V
BV _{CEO}		I _C = 1mA, I _B = 0 I _C = 1mA, I _B = 0	350 400		V V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	6		V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 250V, I_{E} = 0$		50	nA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$		50	nA
h _{FE}	2N6517/2N6517C 2N6517/2N6517C 2N6517/2N6517C 2N6517/2N6517C	$V_{CE} = 10V, I_{C} = 1mA$ $V_{CE} = 10V, I_{C} = 10mA$ $V_{CE} = 10V, I_{C} = 30mA$ $V_{CE} = 10V, I_{C} = 50mA$ $V_{CE} = 10V, I_{C} = 100mA$ $V_{CE} = 10V, I_{C} = 5mA$	20 30 30 20 15 50	200 200 200	

Electrical Characteristics (Continued) $T_a = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Max.	Units
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 10mA, I _B = 1mA		0.3	V
(3.3.3)		$I_{C} = 20 \text{mA}, I_{B} = 2 \text{mA}$		0.35	V
		$I_{C} = 30 \text{mA}, I_{B} = 3 \text{mA}$		0.5	V
		$I_C = 50$ mA, $I_B = 5$ mA		1	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 10mA, I _B = 1mA		0.75	V
(;;;)		$I_{C} = 20 \text{mA}, I_{B} = 2 \text{mA}$		0.85	V
		$I_C = 30\text{mA}, I_B = 3\text{mA}$		0.9	V
C _{ob}	Output Capatitance	V _{CB} = 20V, I _E = 0, f = 1MHz		6	pF
f _T	Current Gain Bandwidth Product *	$I_C = 10 \text{mA}, V_{CE} = 20 \text{V}, f = 20 \text{MHz}$	40	200	MHz
V _{BE(on)}	Base-Emitter On Voltage	I _C = 100mA, V _{CE} = 10V		2	V

^{*} Pulse Test: Pulse Width $\leq 300 \mu s,$ Duty Cycle $\leq 2\%$

Typical Performance Characteristics

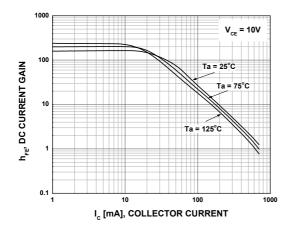


Figure 1. DC Current Gain

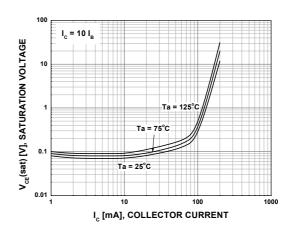


Figure 2. Saturation Voltage

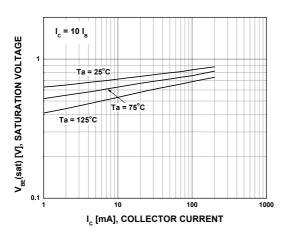


Figure 3. Saturation Voltage

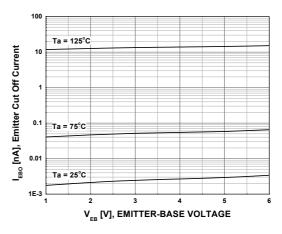


Figure 4. Emitter Cut Off Current

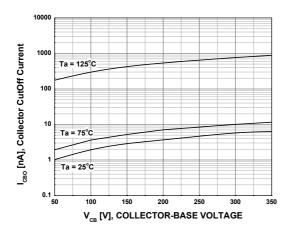


Figure 5. Collector CutOff Current

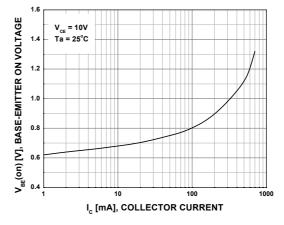


Figure 6. Base-Emitter On Voltage

Typical Performance Characteristics (Continued)

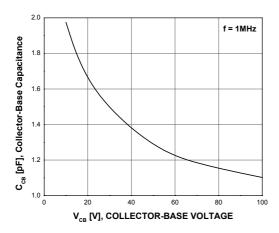


Figure 7. Output Capacitance

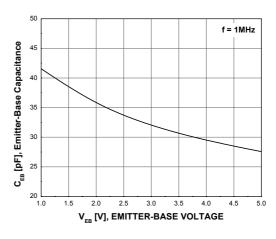


Figure 8. Input Capacitance

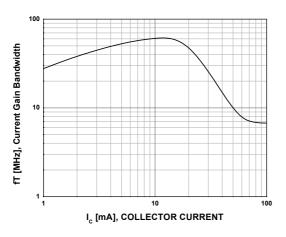


Figure 9. Current Gain Bandwidth Product

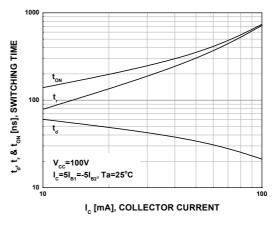


Figure 10. Resistive Load Switching

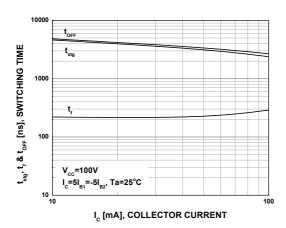
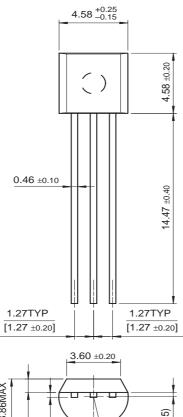
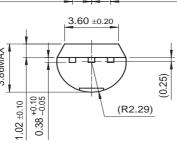


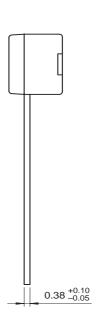
Figure 11. Resistive Load Switching

Physical Dimensions

TO-92







Dimensions in Millimeters





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